

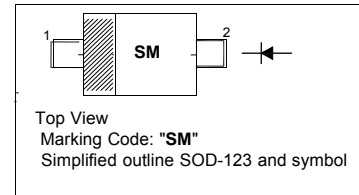
## Surface Mount Schottky Barrier Diode

### Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	60	V
Working Peak Reverse Voltage	$V_{RWM}$	60	V
DC Blocking Voltage	$V_R$	60	V
RMS Reverse Voltage	$V_{R(RMS)}$	42	V
Average Rectified Forward Current	$I_{F(AV)}$	15	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	50 2	mA A
		at $t = 1\text{ s}$ at $t = 10\text{ }\mu\text{s}$	
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Power Dissipation	$P_{tot}$	333	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	60	-	V
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	$V_F$	- -	0.41 1	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	-	200	nA
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$ , $I_{tr} = 0.1X I_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	1	ns

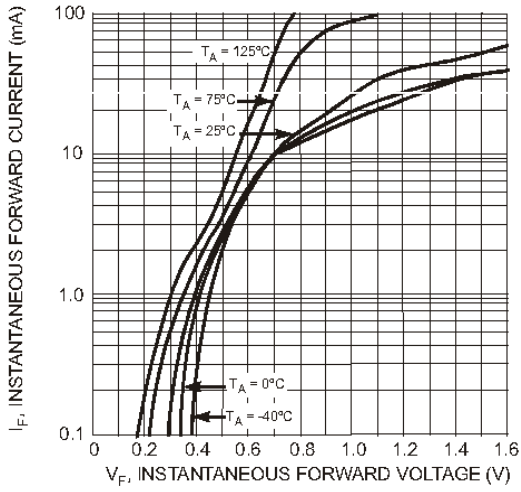


Fig. 1 Typical Forward Characteristics

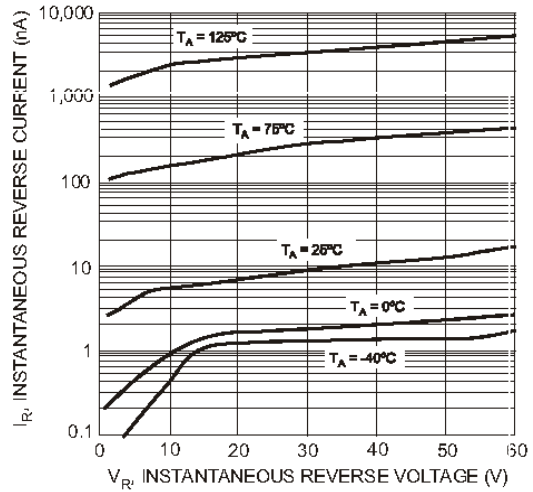


Fig. 2 Typical Reverse Characteristics

